



# STL140N4LLF5

N-channel 40 V, 0.00275  $\Omega$ , 32 A, PowerFLAT™ 5x6  
STripFET™ V Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub>
STL140N4LLF5	40 V	0.00275 $\Omega$	32 A <sup>(1)</sup>

1. The value is rated according R<sub>thj-pcb</sub>.

- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- High avalanche ruggedness
- Low gate drive power losses

## Applications

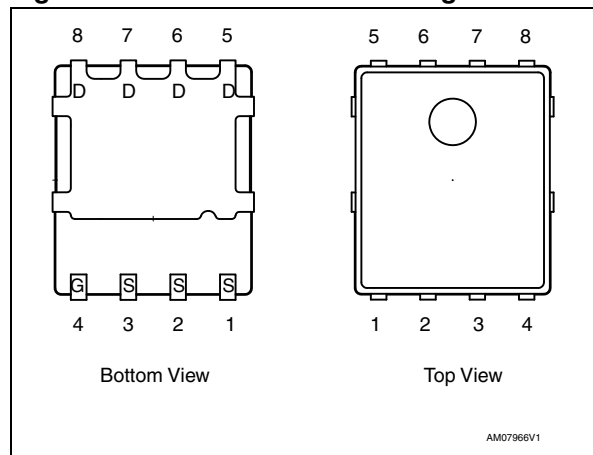
- Switching applications

## Description

This device is an N-channel Power MOSFET developed using STMicroelectronics' STripFET™V technology. The device has been optimized to achieve very low on-state resistance, contributing to an FOM that is among the best in its class.



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

Order code	Marking	Package	Packaging
STL140N4LLF5	140N4LLF5	PowerFLAT™ 5x6	Tape and reel

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	40	V
$V_{GS}$	Gate-source voltage	$\pm 22$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	140	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	88	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	32	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	20	A
$I_{DM}^{(3)}$	Drain current (pulsed)	128	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	80	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4	W
	Derating factor	0.03	W/ $^\circ\text{C}$
$T_J$	Operating junction temperature	-55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		

1. The value is rated according to  $R_{thj-c}$
2. The value is rated according to  $R_{thj-pcb}$
3. Pulse width limited by safe operating area

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (drain, steady state)	1.56	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	31.3	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ sec}$

**Table 4. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AV}$	Not-repetitive avalanche current, (pulse width limited by $T_J\text{ max}$ )	16	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AV}$ , $V_{DD} = 24\text{ V}$ )	300	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0$	40			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 40\ \text{V}$ , $V_{DS} = 40\ \text{V}$ at $T_C = 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 22\ \text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\ \text{V}$ , $I_D = 16\ \text{A}$ $V_{GS} = 4.5\ \text{V}$ , $I_D = 16\ \text{A}$		0.0021 0.0024	0.00275 0.0031	$\Omega$ $\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\ \text{V}$ , $f = 1\ \text{MHz}$ , $V_{GS} = 0$		5900		pF
$C_{oss}$	Output capacitance		-	870	-	pF
$C_{rss}$	Reverse transfer capacitance				130	pF
$Q_g$	Total gate charge	$V_{DD} = 15\ \text{V}$ , $I_D = 32\ \text{A}$ $V_{GS} = 4.5\ \text{V}$ (see Figure 14)		45		nC
$Q_{gs}$	Gate-source charge		-	14	-	nC
$Q_{gd}$	Gate-drain charge				17	nC
$R_G$	Gate input resistance	$f = 1\ \text{MHz}$ Gate DC Bias = 0 Test signal level = 20 mV open drain	-	1.2	-	$\Omega$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=15\text{ V}$ , $I_D=16\text{ A}$ , $R_G=4.7\ \Omega$ , $V_{GS}=10\text{ V}$ <i>(see Figure 13)</i>		19		ns
$t_r$	Rise time			29		ns
$t_{d(off)}$	Turn-off delay time		-	90	-	ns
$t_f$	Fall time			21		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		18	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		72	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 32\text{ A}$ , $V_{GS}=0$	-		1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 32\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 25\text{ V}$		44		ns
$Q_{rr}$	Reverse recovery charge		-	57		nC
$I_{RRM}$	Reverse recovery current			2.6		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

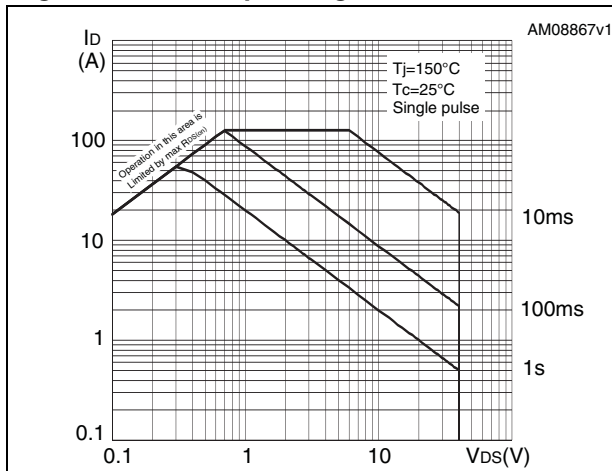


Figure 3. Thermal impedance

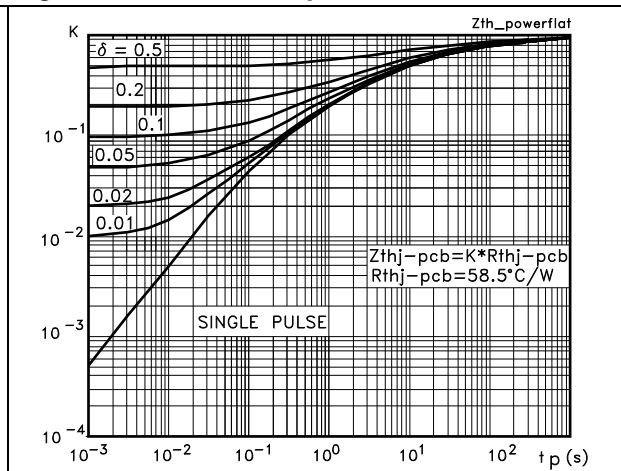


Figure 4. Output characteristics

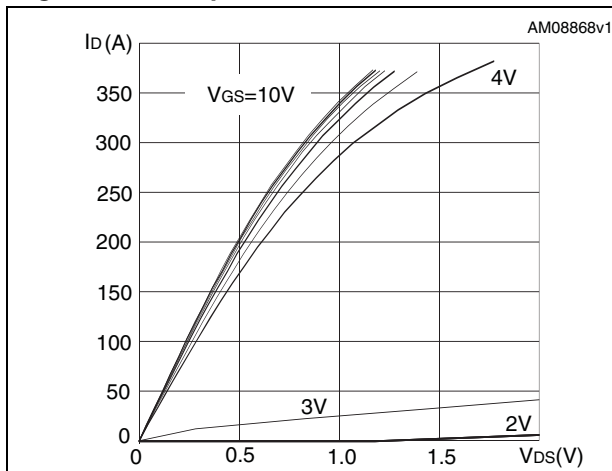


Figure 5. Transfer characteristics

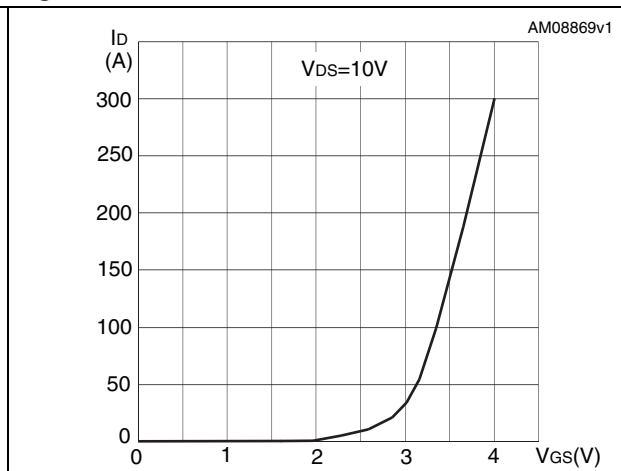


Figure 6. Normalized  $BV_{DSS}$  vs temperature

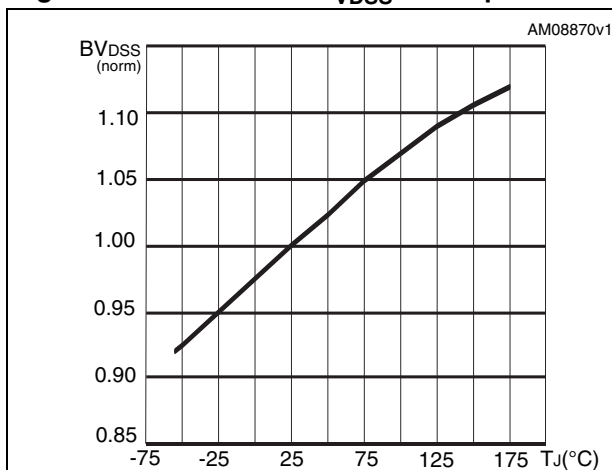


Figure 7. Static drain-source on resistance

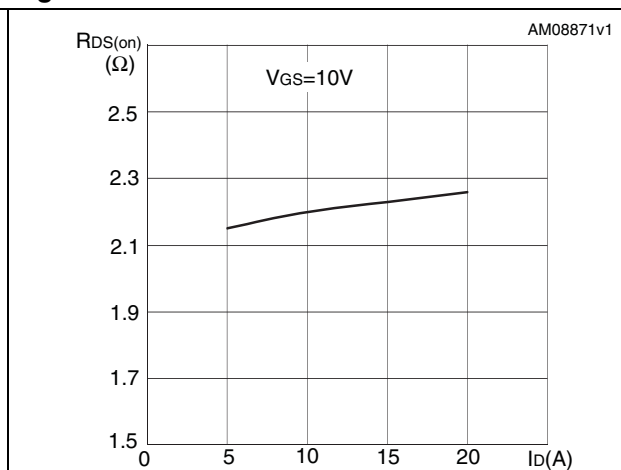


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

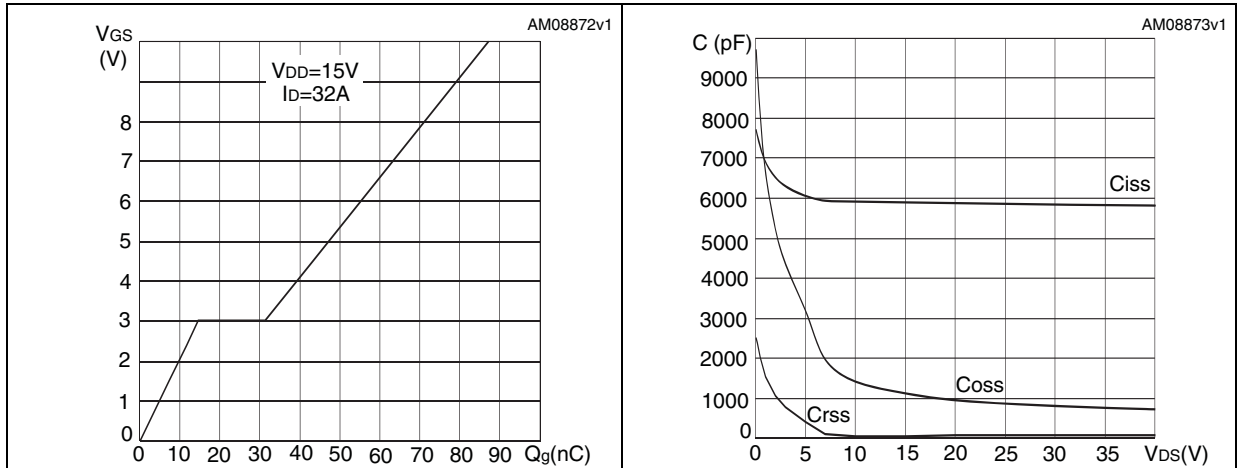


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

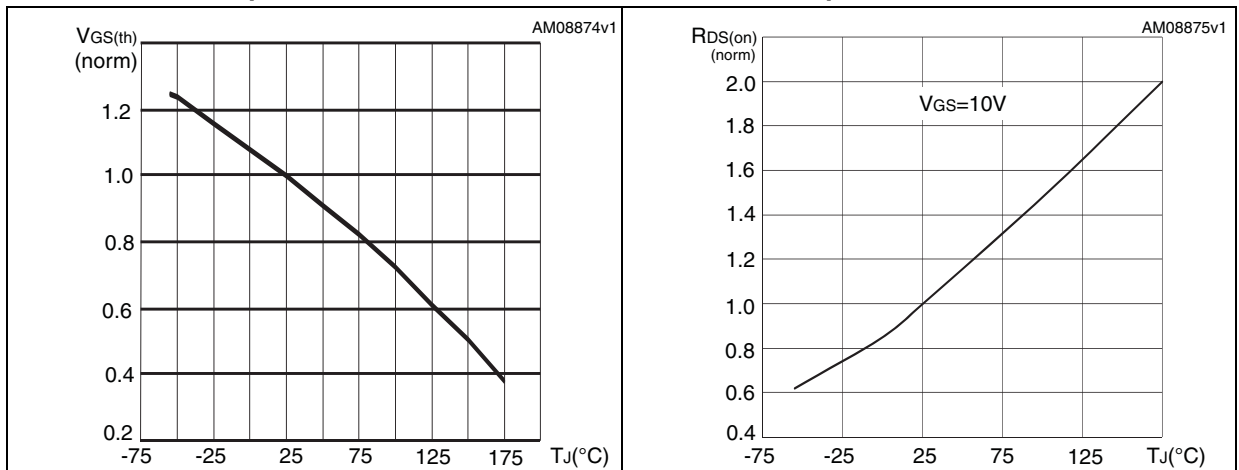
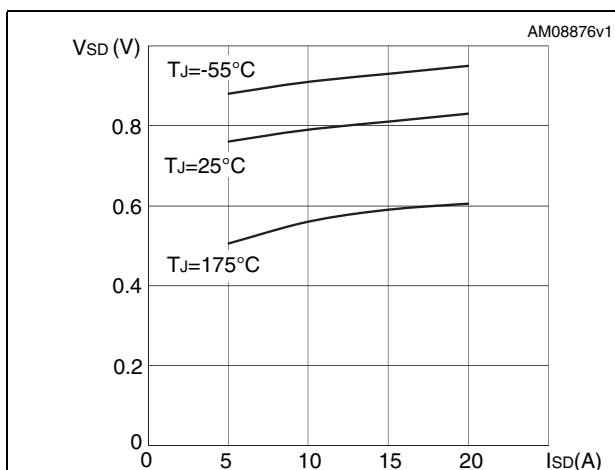
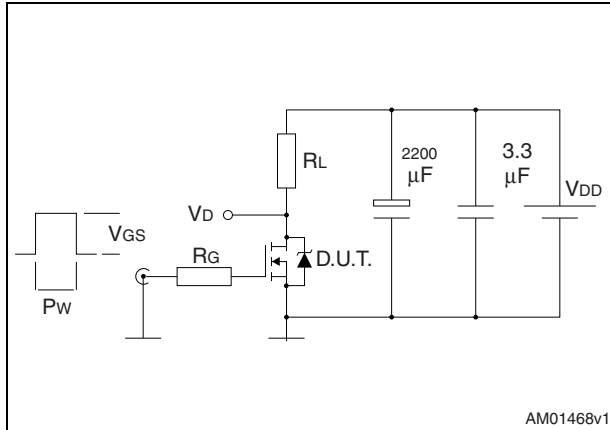


Figure 12. Source-drain diode forward characteristics

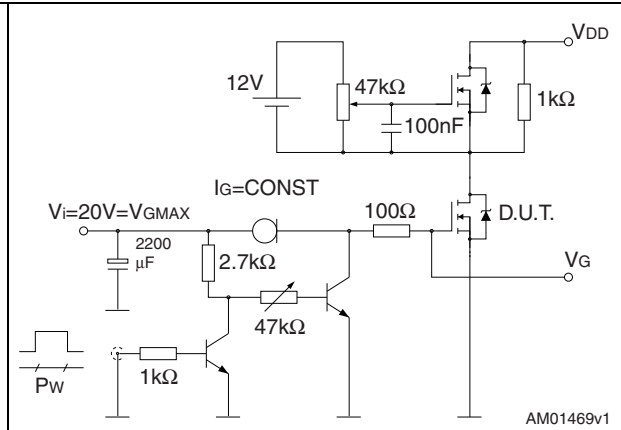


### 3 Test circuits

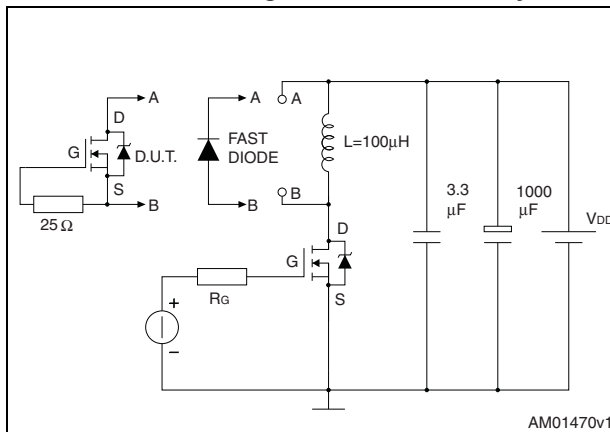
**Figure 13. Switching times test circuit for resistive load**



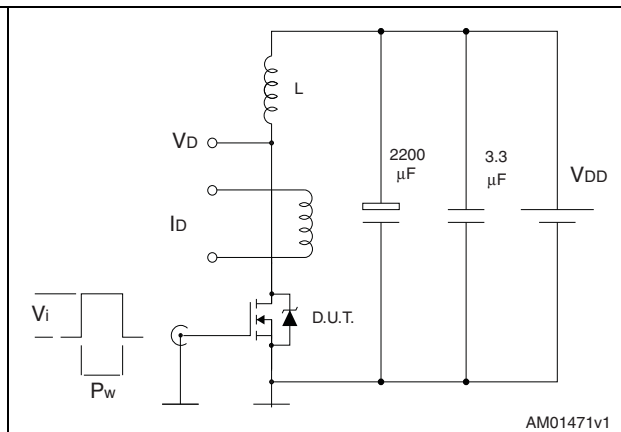
**Figure 14. Gate charge test circuit**



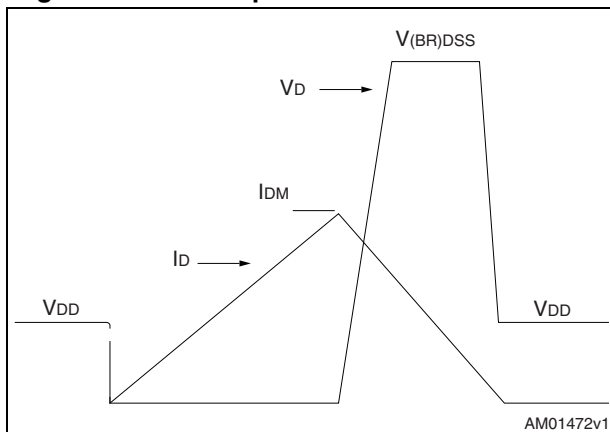
**Figure 15. Test circuit for inductive load switching and diode recovery times**



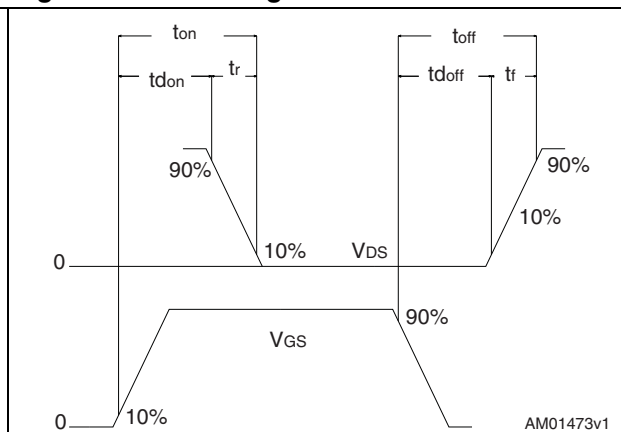
**Figure 16. Unclamped inductive load test circuit**



**Figure 17. Unclamped inductive waveform**



**Figure 18. Switching time waveform**



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

Table 9. PowerFLAT™ 5x6 type C-B mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.83	0.93
A1	0	0.02	0.05
A3		0.20	
b	0.35	0.40	0.47
D		5.00	
D1		4.75	
D2	4.15	4.20	4.25
E		6.00	
E1		5.75	
E2	3.43	3.48	3.53
E4	2.58	2.63	2.68
e		1.27	
L	0.70	0.80	0.90

Figure 19. PowerFLAT™ 5x6 type C-B drawing

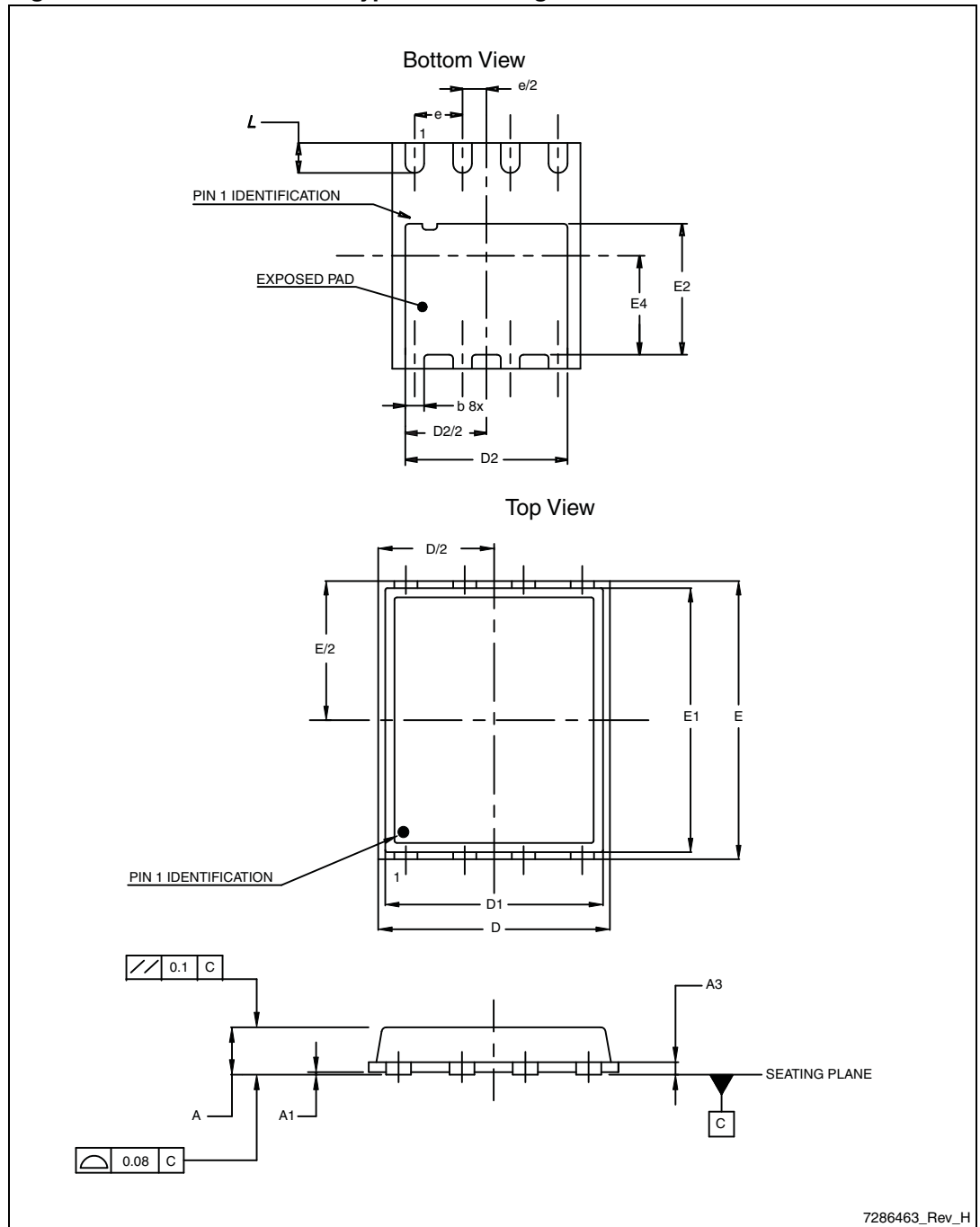


Table 10. PowerFLAT™ 5x6 type S-C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
E		6.15	
D2	4.11		4.31
E2	3.50		3.70
e		1.27	
e1		0.65	
L	0.715		1.015
K	1.05		1.35

Figure 20. PowerFLAT™ 5x6 type S-C mechanical data

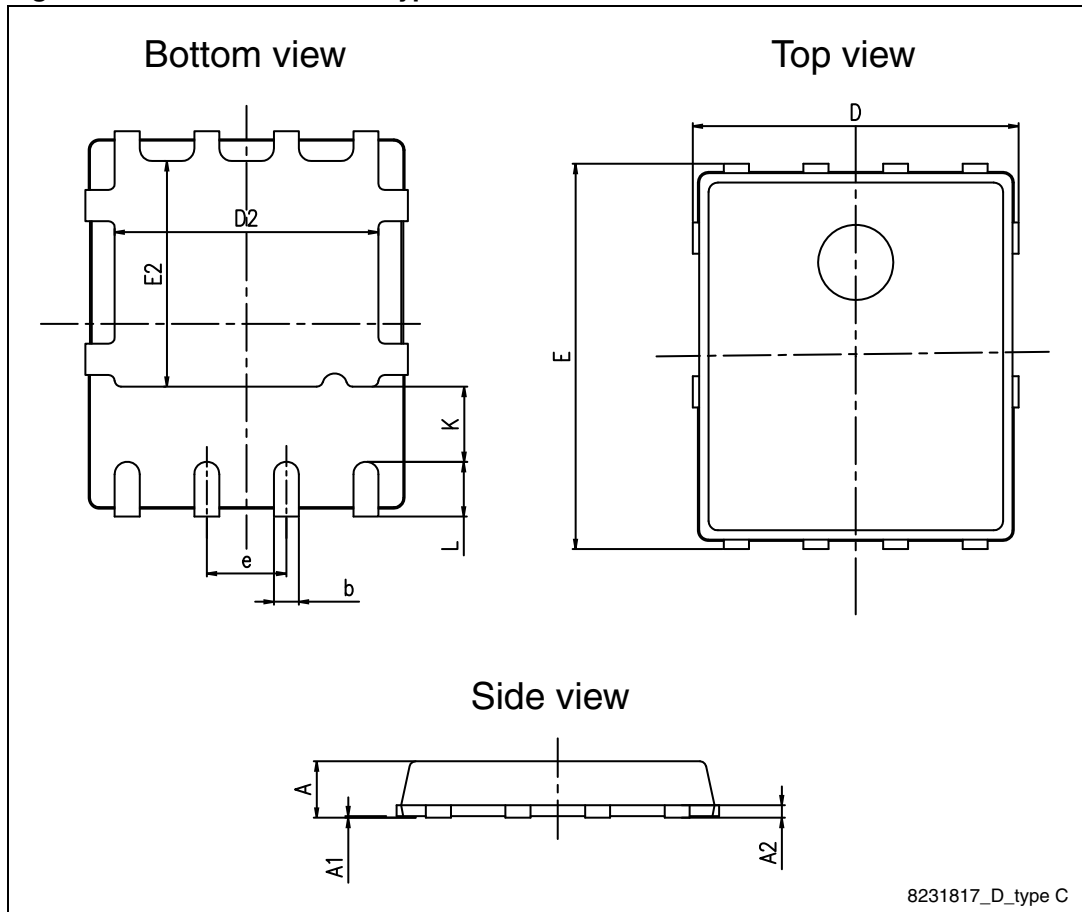
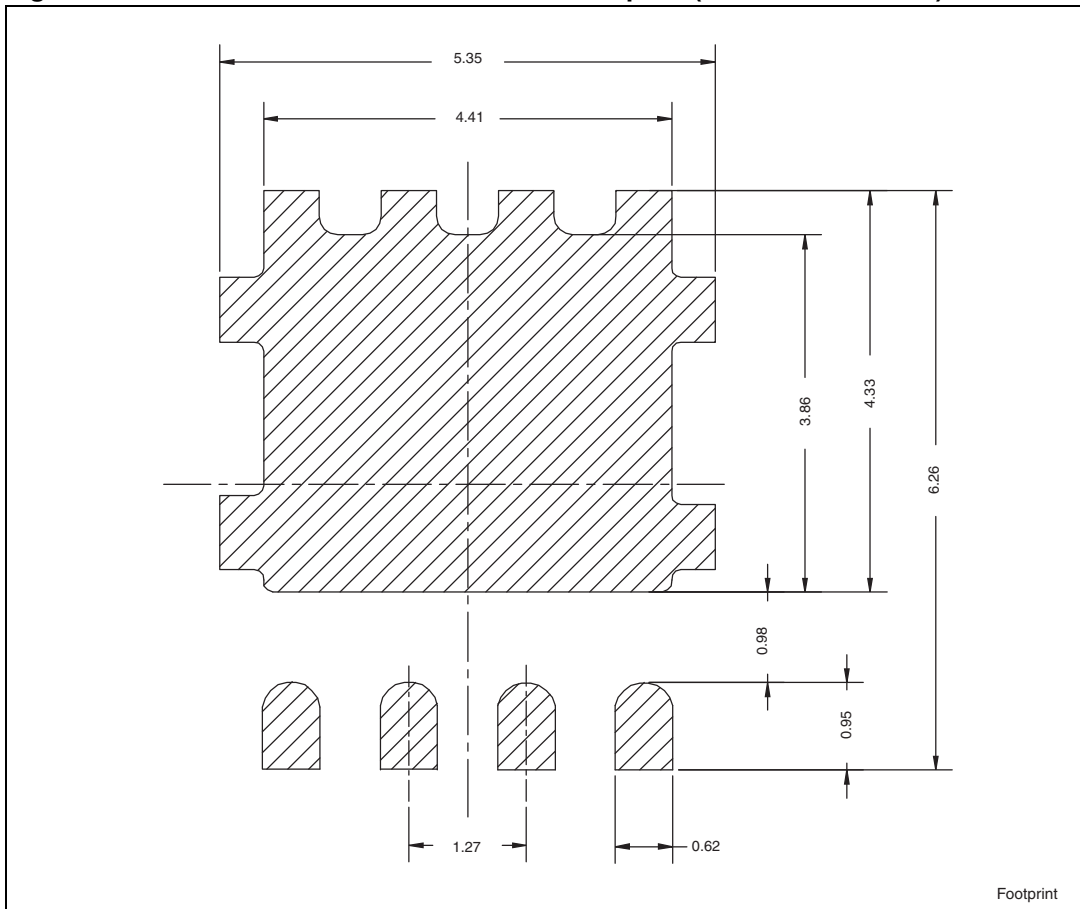


Figure 21. PowerFLAT™ 5x6 recommended footprint (dimensions in mm)



## 5 Revision history

Table 11. Document revision history

Date	Revision	Changes
03-Jun-2010	1	First release.
29-Apr-2011	2	Document status promoted from preliminary data to datasheet.
10-Nov-2011	3	<i>Section 4: Package mechanical data</i> has been updated. Minor text changes.

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